

Product Overview

FDD10N20LZ: Power MOSFET, N-Channel, Logic Level, UniFET™, 200 V, 7.6 A, 360 mΩ, DPAK

For complete documentation, see the data sheet.

UniFET™ MOSFET is an high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

Features

- RDS(on) = 300mΩ (Typ.)@ VGS = 10V, ID = 3.8A
- Low gate charge (Typ. 12nC)
- Low Crss (Typ. 11pF)
- 100% avalanche tested
- Improved dv/dt capability
- ESD improved capability
- RoHS compliant

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V _{DS(BR)} Min (V)	V _{GS} Max (V)	V _{GS(th)} Max (V)	I _D Max (A)	P _D Max (W)	R _{DS(on)} Max @ V _{GS} = 2.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 4.5 V (mΩ)	R _{DS(on)} Max @ V _{GS} = 10 V (mΩ)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	C _{iss} Typ (pF)	Package Type
FDD10N20LZTM	0.3185	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Single	200	±20	3	7.6	83	-	400	360	-	12	440	DPAK-3 / TO-252-3

For more information please contact your local sales support at www.onsemi.com.

Created on: 3/8/2021